



# 제 29회 한국반도체학술대회

The 29th Korean Conference on Semiconductors

2022년 1월 24일(월)~ 26일(수) | 강원도 하이원 그랜드호텔(컨벤션타워)

2022년 1월 25일(화), 10:45-12:15

Room L (다이아몬드 II, 6층)

## C. Material Growth & Characterization 분과

### [TL2-C] 2D Materials

좌장: 김튼튼 교수(울산대학교)

<p><b>TL2-C-1</b> 10:45-11:15</p>	<p><b>Epitaxial Chalcogenide Films and Their Band Structure Properties</b> Young Jun Chang<sup>1</sup>, In Hak Lee<sup>2</sup>, and Byoung Ki Choi<sup>1,3</sup> <i><sup>1</sup>Department of Physics and Smart Cities, University of Seoul, <sup>2</sup>Center for Spintronics, KIST, <sup>3</sup>Advanced Light Source, Lawrence Berkeley National Laboratory</i></p>
<p><b>TL2-C-2</b> 11:15-11:30</p>	<p><b>Thru-Hole Epitaxy as an Alternative to Remote Epitaxy</b> Dongsoo Jang<sup>1</sup>, Chulwoo Ahn<sup>2</sup>, Youngjun Lee<sup>1</sup>, Seungjun Lee<sup>1</sup>, Hyunkyu Lee<sup>2</sup>, Donghoi Kim<sup>2</sup>, Young-Kyun Kwon<sup>1,2</sup>, Jaewu Choi<sup>2</sup>, and Chinkyoo Kim<sup>1,2</sup> <i><sup>1</sup>Department of Physics, Kyung Hee University, <sup>2</sup>Department of Information Display, Kyung Hee University</i></p>
<p><b>TL2-C-3</b> 11:30-11:45</p>	<p><b>High Growth Rate of <math>\beta</math>-Ga<sub>2</sub>O<sub>3</sub> Epitaxial Layer Grown on (001) <math>\beta</math>-Ga<sub>2</sub>O<sub>3</sub> Substrate by Suppressing a Pre-reaction of Precursors</b> Hyeong-Yun Kim<sup>1,2</sup>, Sunjae Kim<sup>1,3</sup>, Jae-Hyeong Lee<sup>1,4</sup>, Min-Ji Oh<sup>1</sup>, Ji-Hyeon Park<sup>1</sup>, and Dae-Woo Jeon<sup>1</sup> <i><sup>1</sup>KICET, <sup>2</sup>Pukyong National University, <sup>3</sup>Korea Aerospace University, <sup>4</sup>Andong National University</i></p>
<p><b>TL2-C-4</b> 11:45-12:00</p>	<p><b>Large-scale Growth of Si-doped <math>\alpha</math>-Ga<sub>2</sub>O<sub>3</sub> by HVPE</b> Jae-Hyeong Lee<sup>1,2</sup>, Sunjae Kim<sup>1,3</sup>, Hyeong-Yun Kim<sup>1,4</sup>, Min-Ji Oh<sup>1</sup>, Dae-Woo Jeon<sup>1</sup>, and Ji-Hyeon Park<sup>1</sup> <i><sup>1</sup>KICET, <sup>2</sup>Andong National University, <sup>3</sup>Korea Aerospace University, <sup>4</sup>Pukyong National University</i></p>
<p><b>TL2-C-5</b> 12:00-12:15</p>	<p><b>Growth Issue for Realization of High-Q Hexagonal Boron Nitride Microresonator by Direct Growth Method</b> Jaehyun Park<sup>1</sup> and Paul E. Barclay<sup>2</sup> <i><sup>1</sup>Materials Architecturing Research Center, KIST, <sup>2</sup>Institute for Quantum Science and Technology, University of Calgary</i></p>